

Schottky Barrier Diode

FF1J9

Features

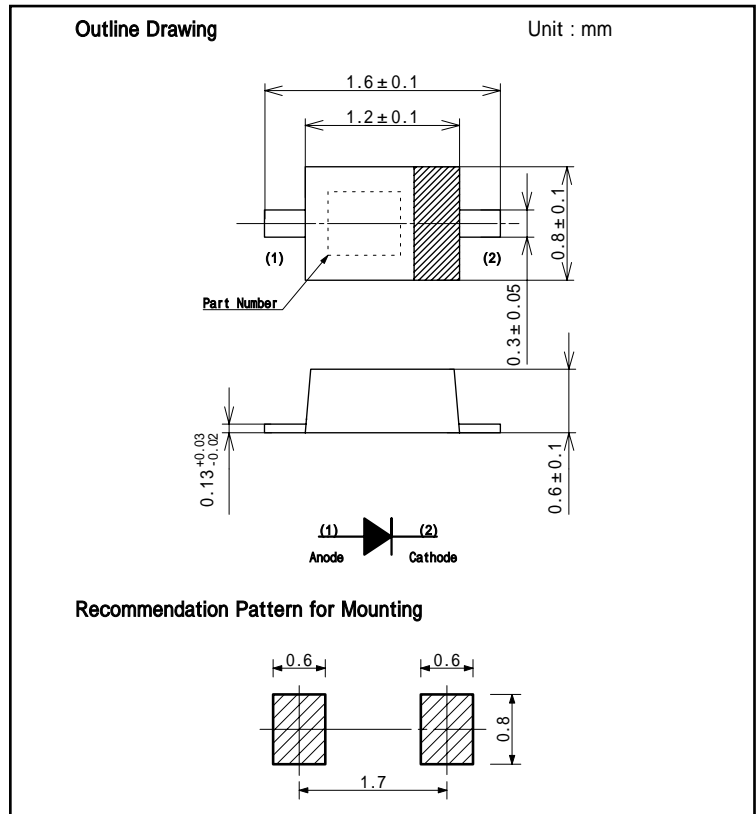
- Super small size
- Various kinds
- Taping capable of high density mounting

Applications

- Small size power supplies
- OR diode: Preventing from reverse current by wrong setting of a battery .

Structures

- Resin molded, and Silicon Schottky Barrier Diode.
- Marking symbol : [E]
- Terminal plating : Sn-2Bi
- Conforms to RoHS regulations



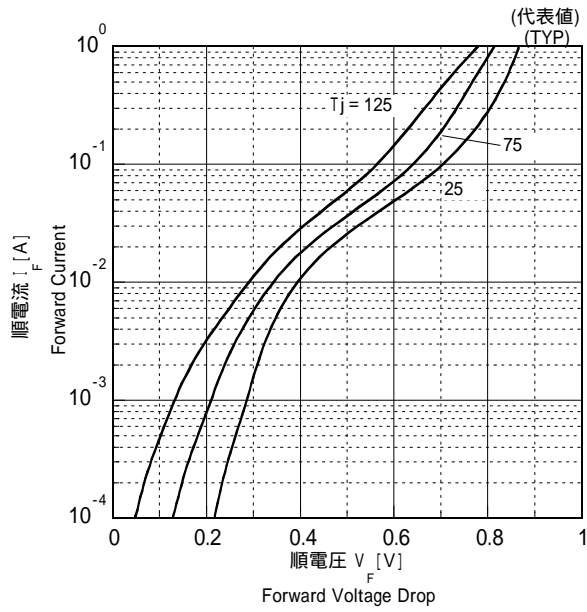
Absolute Maximum Ratings

Items	Symbol	Conditions	Ratings	Unit
Repetitive Peak Reverse Voltage	V_{RM}		90	V
Non-Repetitive Peak Reverse Voltage	V_{RSM}		95	V
Average Rectified Forward Current	I_O	Ta=25 , Half sin wave 180 ° ,Resistive Load	100	mA
Peak Forward Surge Current	I_{FSM}	Tj=25 , 50Hz, Single-phase, Half sin wave, Non-Repetitive	1	A
Operating Junction Temperature	T_j		-40 ~ +125	
Storage Temperature	T_{stg}		-40 ~ +125	

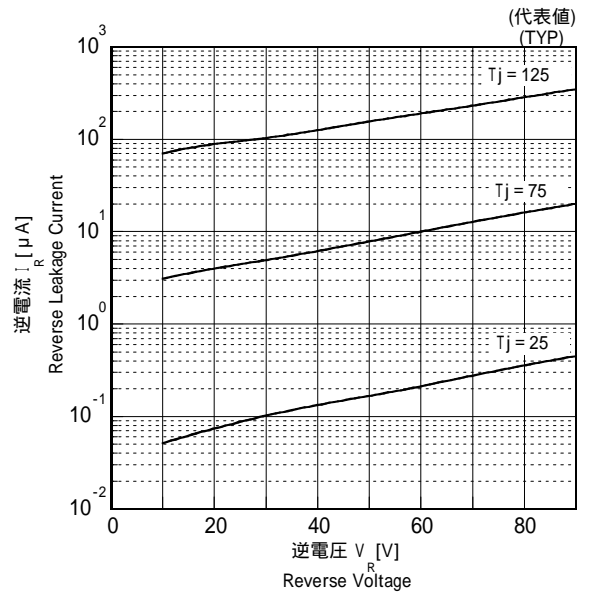
Electrical Characteristics (Tj=25)

Items	Symbol	Conditions	TYP.	MAX.	Unit
Forward Voltage Drop	V_{F1}	$I_f=1mA$	0.29	-	V
	V_{F2}	$I_f=10mA$	0.39	-	V
	V_{F3}	$I_f=100mA$	0.73	0.77	V
Reverse Leakage Current	I_{R1}	$V_R=40V$	0.15	-	μA
	I_{R2}	$V_R=90V$	-	5.0	μA
Junction Capacitance	C_j	$V_R=10V, f=1MHz$	8.0	-	pF
Thermal resistance	Rth(j-a)	Glass Epoxy Substrate, PC board : 20mm, Cu land : 4mm	-	400	/W

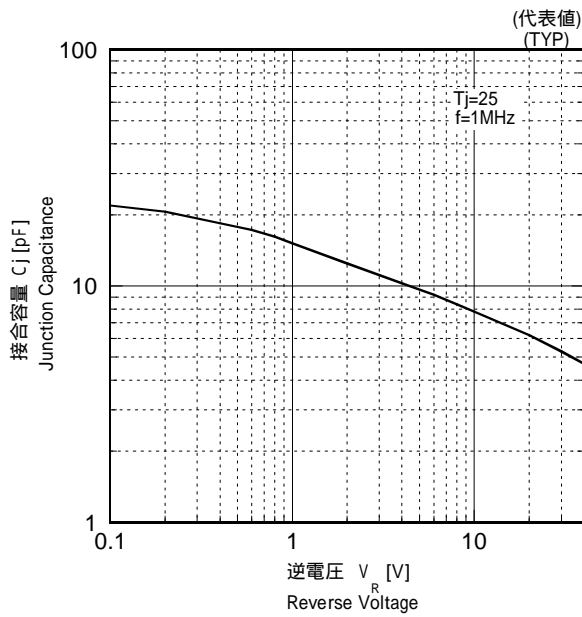
Characteristics Diagrams



FORWARD CHARACTERISTICS



REVERSE CHARACTERISTICS



TYPICAL JUNCTION CAPACITANCE